

Fig. 1A

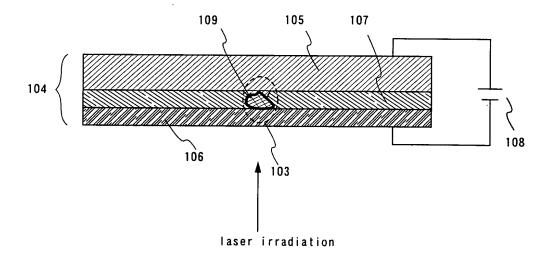


Fig. 1B

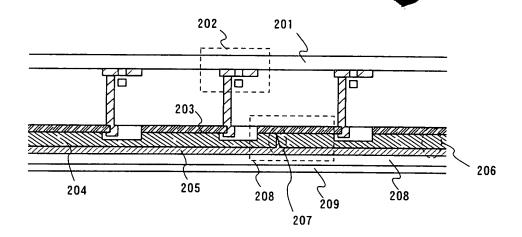


Fig. 2A

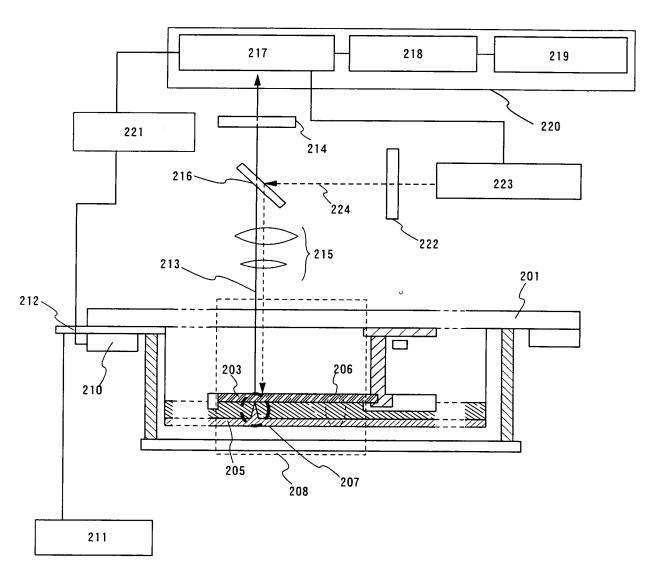


Fig. 2B

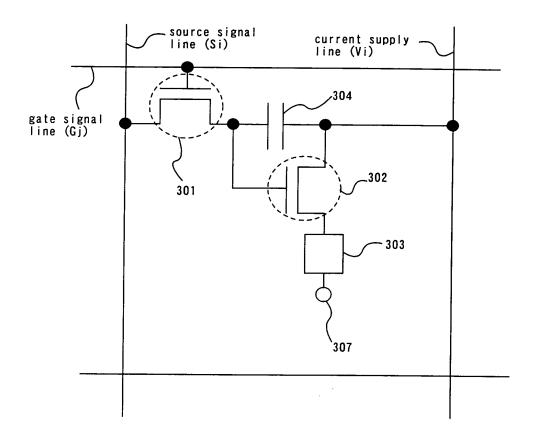
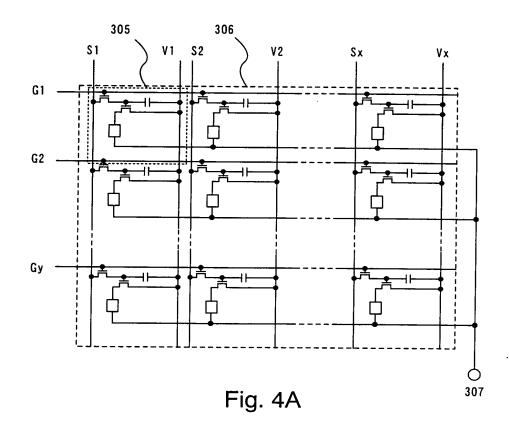


Fig. 3



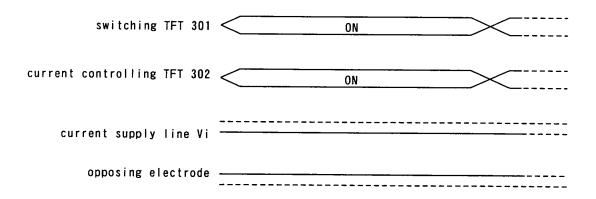
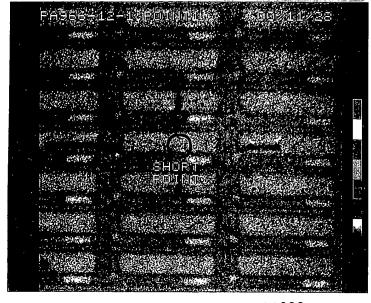


Fig. 4B



 $\times 200$

Fig. 5A

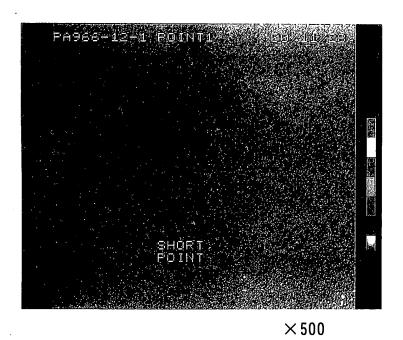


Fig. 5B

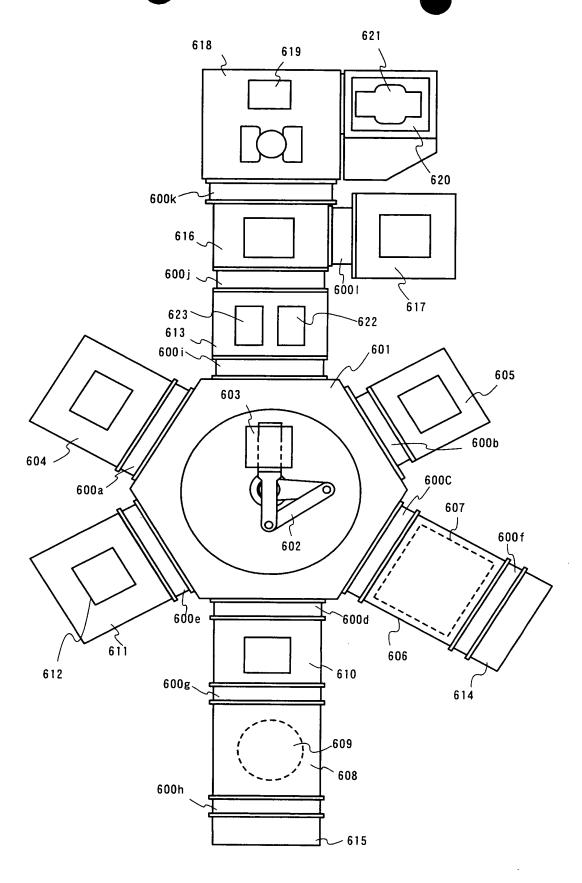


Fig. 6

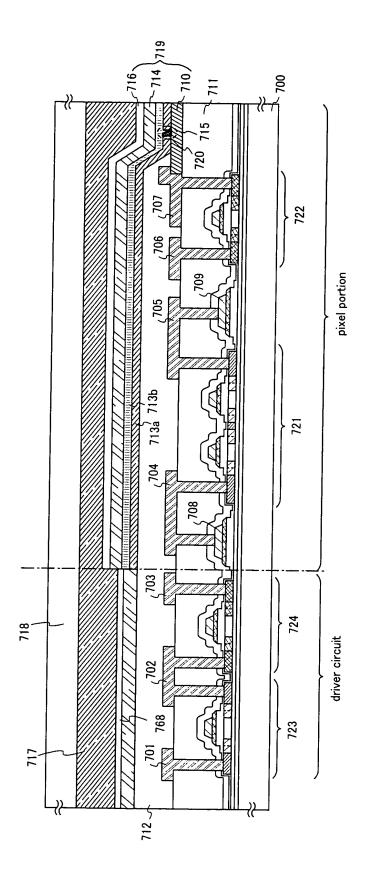
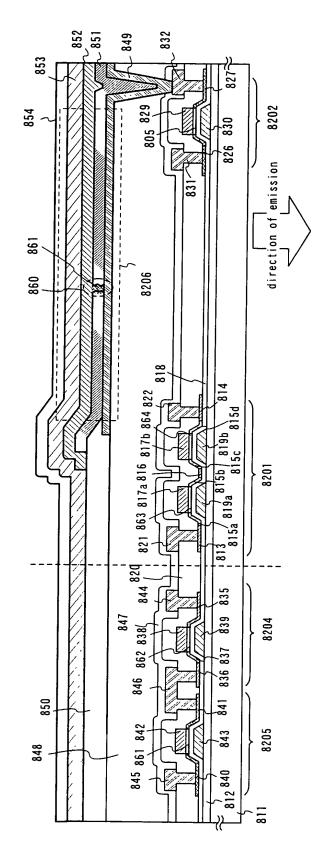
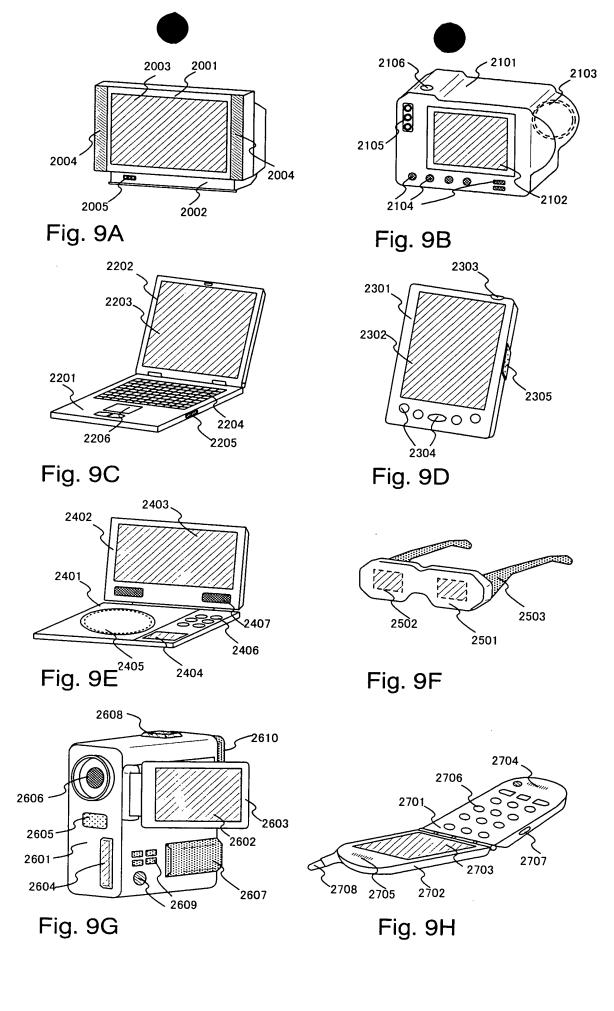


Fig. 7



843:gate electrode 844,845:source wirings 846:drain wiring 847.first passivation film 848:second interlayer insulating film 811: substrate 812: base film 813: source region 814: drain region 815a—815d: LDD region 816: separation region 818: gate insulating film 819a, 819b: gate electrodes 820: first interlayer insulating film 821: source signal line 822: drain wiring 826: source region 827: drain region 828: LDD region 829: channel formation region 830: gate electrode 831: source wiring 832: drain wiring 835: source region 836: drain region 837: LDD region 837: LDD region 838: channel formation region 838: channel formation region 849:pixel electrode (anode) 850:third interlayer insulating film 851:organic compound layer 852:cathode 853:protecting electrode 854:second passivation film

Fig. 8



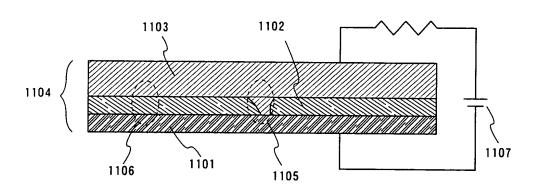


Fig. 10A

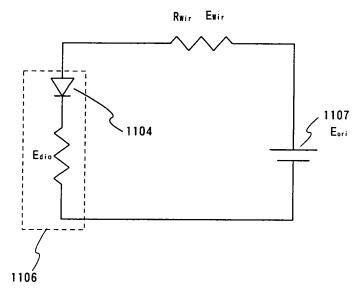


Fig. 10B

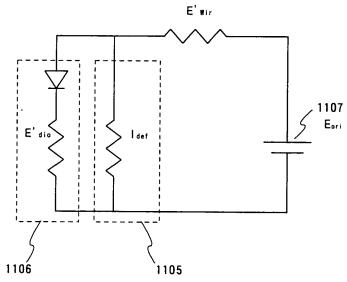


Fig. 10C

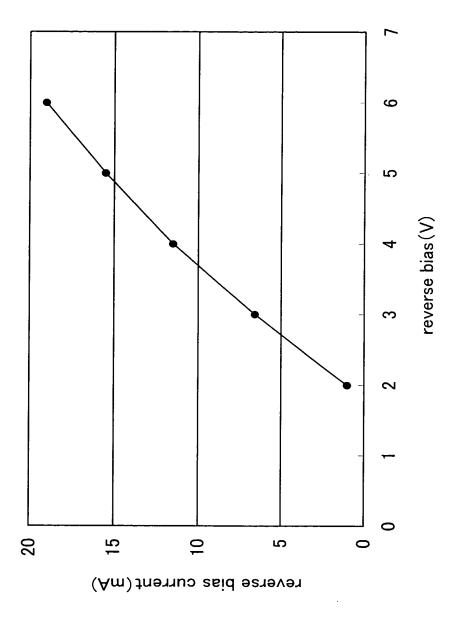


Fig. 11 Current property when a backward bias voltage is applied to a light emitting element